

FERROELECTRIC MEMORY DEVICE, METHOD OF MANUFACTURING THE SAME,
AND EMBEDDED DEVICE

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5 The present application includes the entire content of Japanese Patent Application No. 2000-281725 filed on September 18, 2000.

FIELD OF THE INVENTION

10 The present invention relates to a ferroelectric memory device, a method of manufacturing the same, and an embedded device. More particularly, the present invention relates to a simple matrix ferroelectric memory device using only ferroelectric capacitors instead of cell transistors, a method of manufacturing the same, and an embedded device.

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BACKGROUND OF ART

A simple matrix memory cell array using only ferroelectric capacitors instead of cell transistors has a very simple structure and enables a higher degree of integration.
20 Therefore, development of such a memory cell array has been expected.

SUMMARY

25 An objective of the present invention is to provide a ferroelectric memory device including a desired memory cell array, a method of manufacturing the same, and an embedded device.